

Silicon Doping of Epitaxial Layers of Gallium Oxide by MOCVD

A.O. Efimov^{1,3} , S.N. Rodin², W.V. Lundin² , A.Yu. Ivanov¹ , A.V. Sakharov^{2,3},
D.I. Panov¹ , V.A. Spiridonov¹ , P.A. Bogdanov¹ , A.F. Tsatsulnikov³ ,
D.A. Bauman¹ 

¹ Institute of Advanced Data Transfer Systems, ITMO University, Kronverkskiy pr., 49, lit. A, St. Petersburg, 197101, Russia

² Ioffe Institute, Politekhnicheskaya, 26, St. Petersburg, 194021, Russia

³ Submicron Heterostructures for Microelectronics, Research and Engineering Center, Russian Academy of Sciences, Politekhnicheskaya, 26, St. Petersburg, 194021, Russia

Received: May 30, 2025

Corresponding author: [A.O. Efimov](mailto:A.O.Efimov@itmo.ru)

Abstract. The article considers homoepitaxy of beta gallium oxide layers doped with silicon grown by metal organic chemical vapor deposition (MOCVD). Epitaxial growth was carried out on substrates of iron doped gallium oxide. Epitaxial layers at different rates of silicon doping from a diluted monosilane and at different temperatures were obtained. The crystal quality of epitaxial layers was analyzed, as well as mobility of electrons and conductivity were measured. The possibility of controlling the electrical properties (such as electron mobility and conductivity) of homoepitaxial gallium oxide layers doped with silicon during growth by the MOCVD method was demonstrated.

Acknowledgements. The authors acknowledge support from the Russian Science Foundation (project No. 24-12-00229). The authors are grateful to Dr. M.V. Dorogov for his help in obtaining images of layers using the SEM.

Citation: Rev. Adv. Mater. Technol., 2025, vol. 7, no. 3, pp. 141–147

View online: <https://doi.org/10.17586/2687-0568-2025-7-3-141-147>

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